

TGD N-Channel Enhancement Mode Power MOSFET

**Description**

The TGD15H10D uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

**General Features**

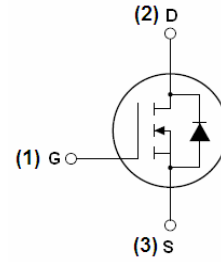
- $V_{DS} = 150V, I_D = 100A$   
 $R_{DS(ON)} < 11m\Omega @ V_{GS} = 10V$  (Typ:9.5m $\Omega$ )
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

**Application**

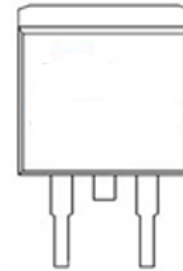
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

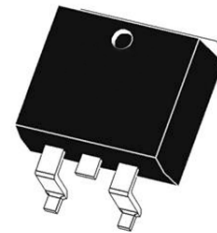
**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



pin assignment



TO-263-2L top view

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
15H10D	15H10D	TO-263-2L	-	-	-

**Absolute Maximum Ratings ( $T_C = 25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	150	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	100	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D (100^\circ C)$	70	A
Pulsed Drain Current	$I_{DM}$	390	A
Maximum Power Dissipation	$P_D$	370	W
Derating factor		2.47	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	1600	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$



**Thermal Characteristic**

Thermal Resistance, Junction-to-Cas <sup>e</sup> (Note 2)	$R_{\theta JC}$	0.41	°C/W
---	-----------------	------	------

**Electrical Characteristics ( $T_C=25^{\circ}C$  unless otherwise noted)**

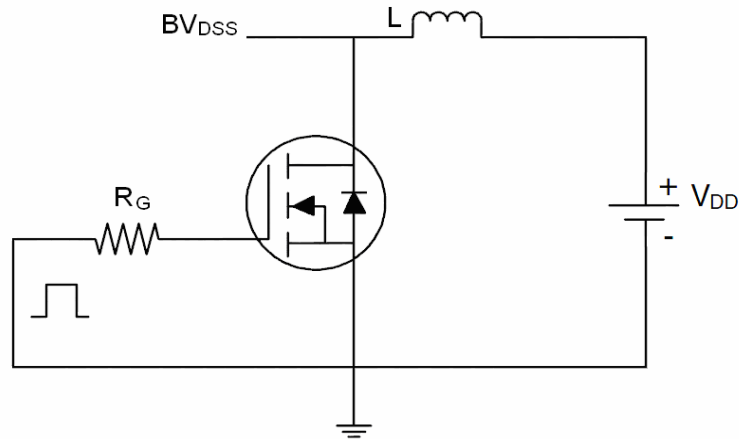
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	150	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=150V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.4	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$	-	9.5	11	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=40A$	100	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	7500	-	PF
Output Capacitance	$C_{oss}$		-	640	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	426	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=75V, I_D=2A, R_L=15\Omega$ $, R_G=2.5\Omega, V_{GS}=10V$	-	32.5	-	nS
Turn-on Rise Time	$t_r$		-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	113	-	nS
Turn-Off Fall Time	$t_f$		-	48	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=75V, I_D=40A,$ $V_{GS}=10V$	-	138	-	nC
Gate-Source Charge	$Q_{gs}$		-	46	-	nC
Gate-Drain Charge	$Q_{gd}$		-	39	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=40A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	100	A
Reverse Recovery Time	$t_{rr}$	$T_j=25^{\circ}C, I_F=40A, di/dt=100A/\mu s$ (Note 3)	-	45		nS
Reverse Recovery Charge	$Q_{rr}$		-	80		nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

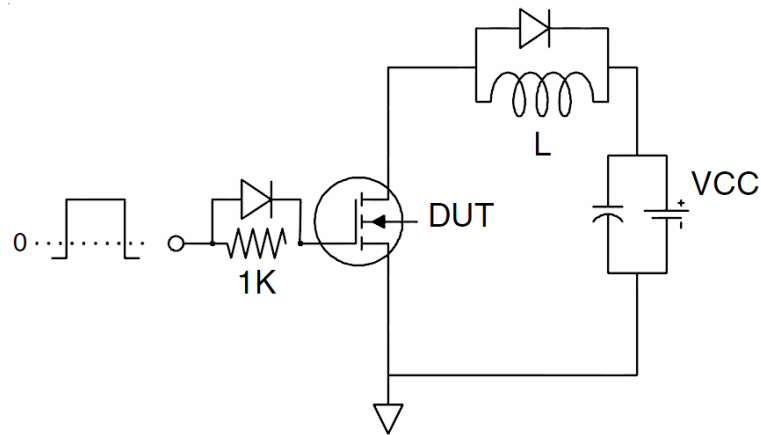
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_j=25^{\circ}C, V_{DS}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

**Test circuit**

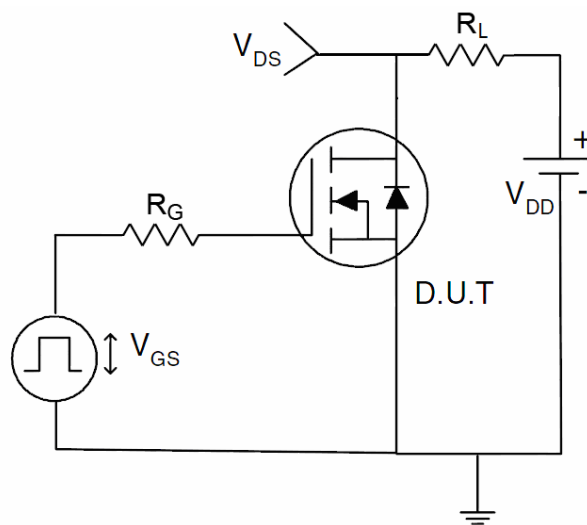
**1) E<sub>AS</sub> test Circuits**



**2) Gate charge test Circuit:**



**3) Switch Time Test Circuit:**



Typical Electrical and Thermal Characteristics (Curves)

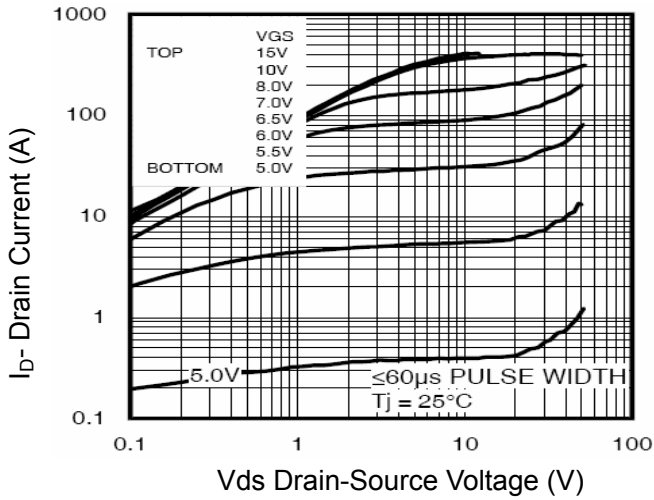


Figure 1 Output Characteristics

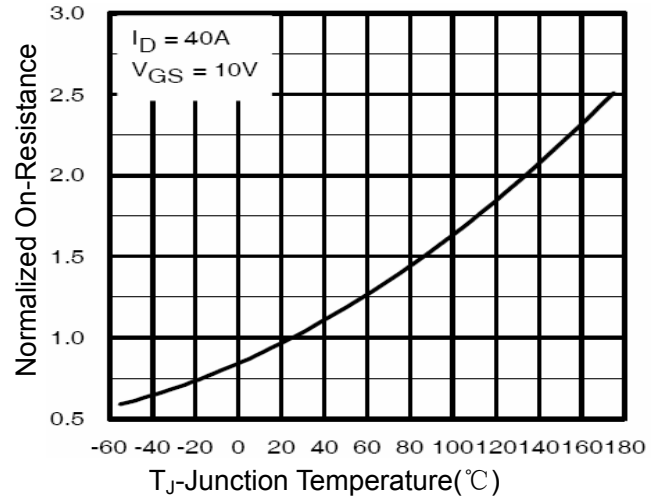


Figure 4 Rdson-Junction Temperature

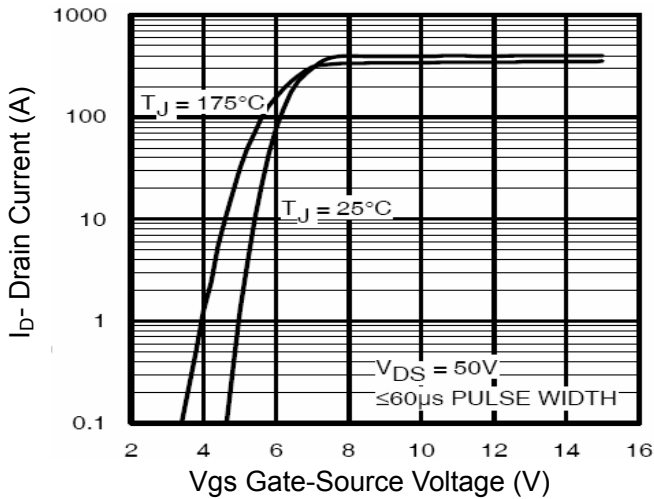


Figure 2 Transfer Characteristics

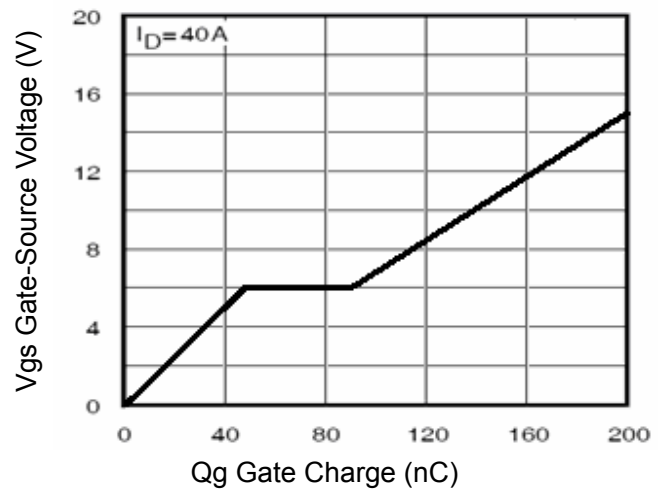


Figure 5 Gate Charge

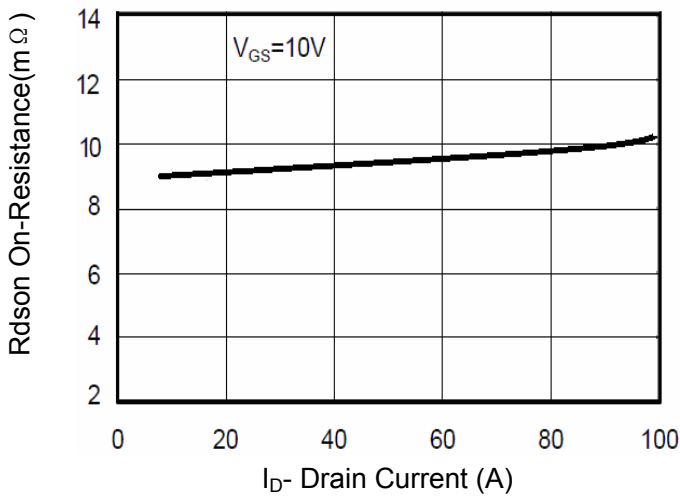


Figure 3 Rdson- Drain Current

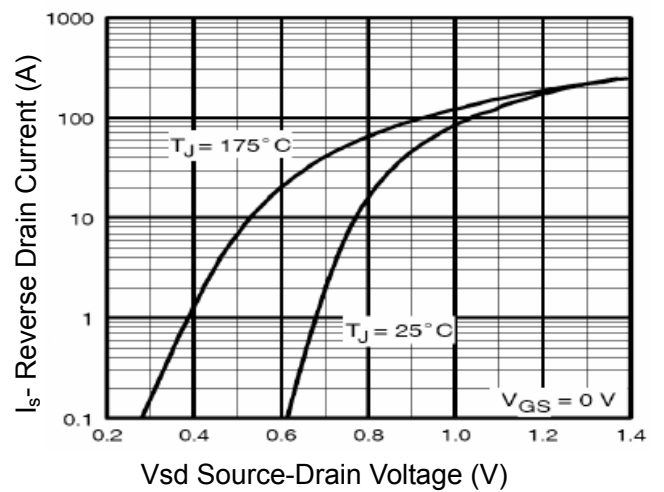


Figure 6 Source- Drain Diode Forward

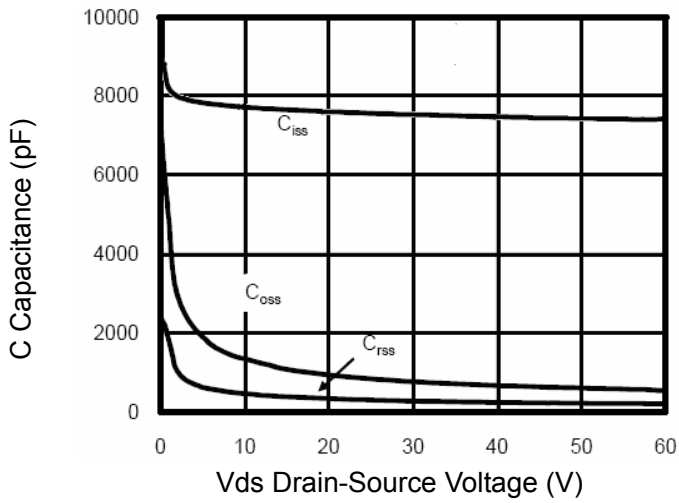


Figure 7 Capacitance vs Vds

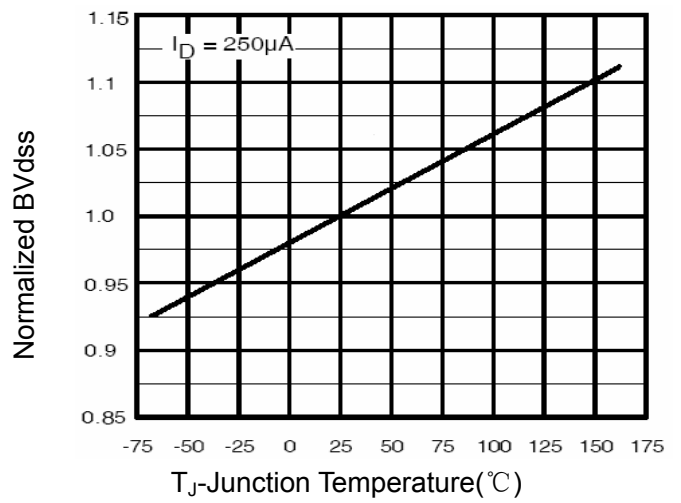


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

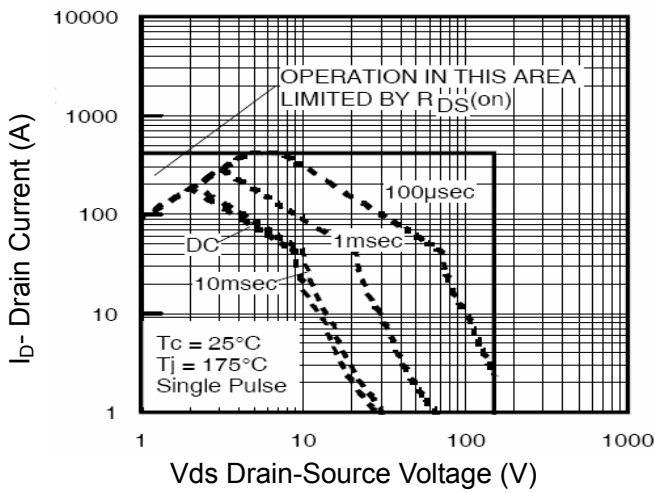


Figure 8 Safe Operation Area

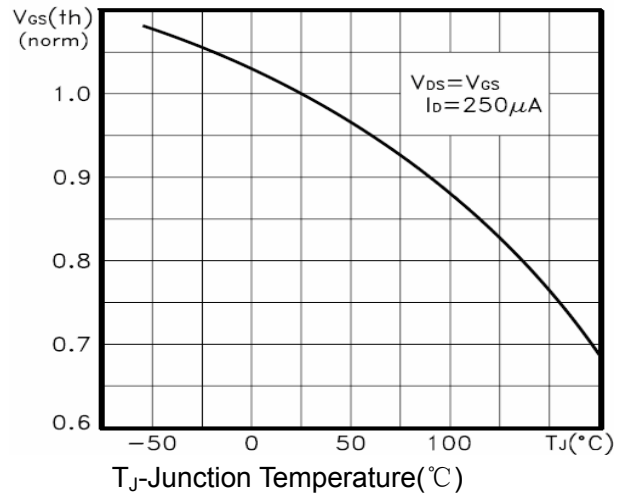


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

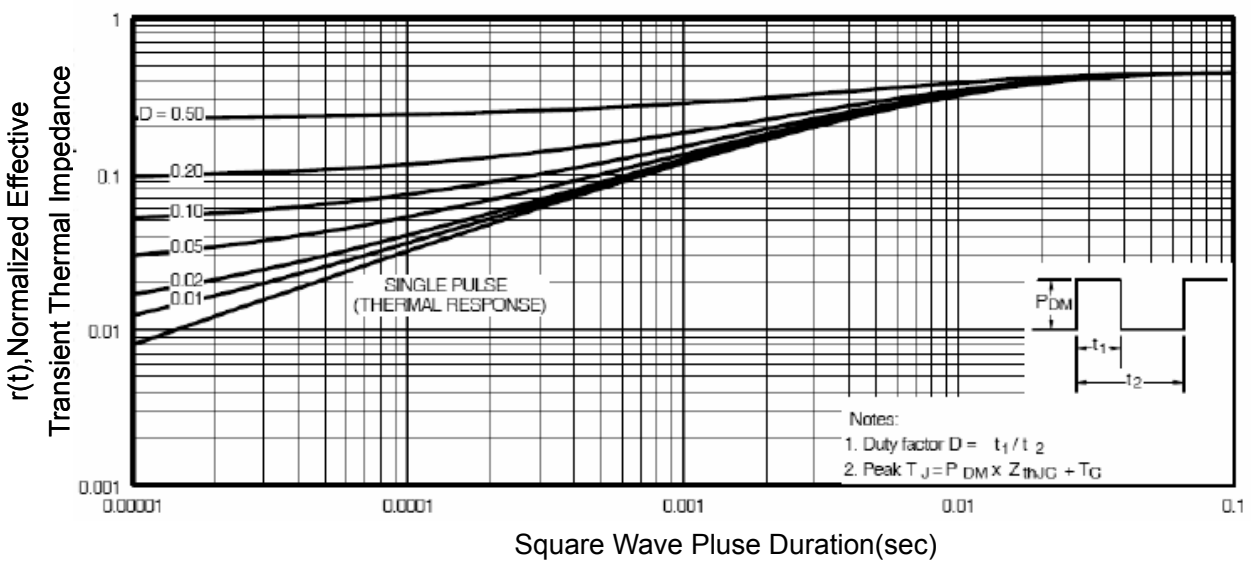
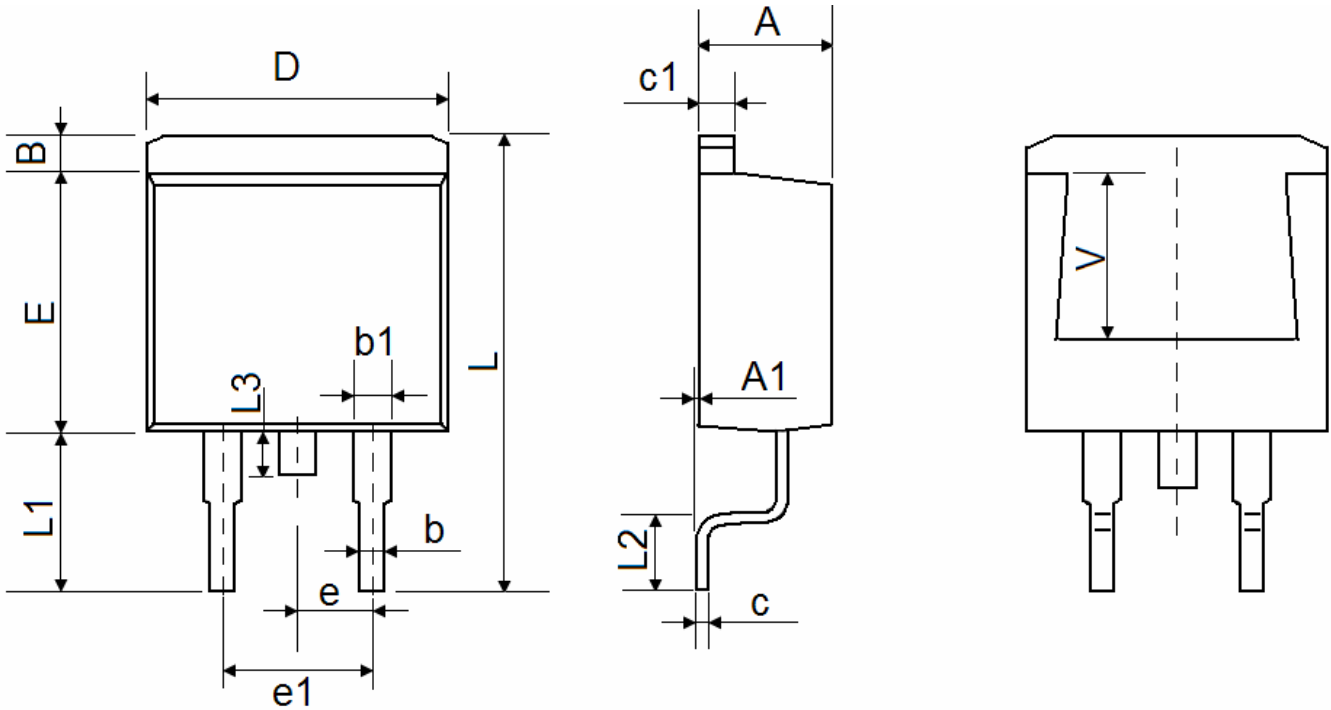


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	